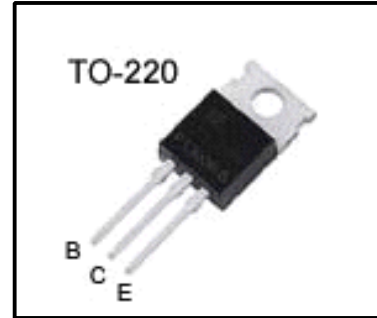*High Voltage Fast-Switching NPN Power Transistor*

Features

■ Very High Switching Speed

■ High Voltage Capability

■ Wide Reverse Bias SOA

General Description

This Device is designed for high voltage, High speed

Switching   characteristics required such as   lighting

system,switching mode power supply.

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Units
V_{CES}	Collector -Emitter Voltage	$V_{BE}=0$	700	V
V_{CEO}	Collector -Emitter Voltage	$I_B=0$	400	V
V_{EBO}	Emitter-Base Voltage	$I_C=0$	9.0	V
I_C	Collector Current		12	A
I_{CP}	Collector pulse Current		25	A
I_B	Base Current		6.0	A
I_{BM}	Base Peak Current	$t_P=5ms$	12	A
P_C	Total Dissipation at Tc*=25℃		100	W
	Total Dissipation at Ta*=25℃		2.2	
T_J	Operation Junction Temperature		-40~150	℃
T_{STG}	Storage Temperature		-40~150	℃

Tc :Case temperature (good cooling)

Ta :Ambient temperature (without heat sink)

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\Theta JC}$	Thermal Resistance Junction to Case	1.25	℃/W
$R_{\Theta JA}$	Thermal Resistance Junction to Ambient	40	℃/W

Electrical Characteristics(Tc=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
$V_{CEO(sus)}$	Collector−Emitter Breakdown Voltage	Ic=10mA,Ib=0	400	−	−	V
$V_{CE(sat)}$	Collector −Emitter Saturation Voltage	Ic=5.0A,Ib=1.0A	−	−	0.5	V
		Ic=8.0A,Ib=1.6A			1.0	
		Ic=12A,Ib=3.0A			1.5	
		Ic=8.0A,Ib=1.6A Tc=100℃	−	−	2.0	V
$V_{BE(sat)}$	Base −Emitter Saturation Voltage	Ic=5.0A,Ib=1.0A	−	−	1.2	V
		Ic=8.0A,Ib=1.6A			1.6	
		Ic=8.0A,Ib=1.6A Tc=100℃	−	−	1.5	V
I_{CBO}	Collector −Base Cutoff Current (Vbe=−1.5V)	Vcb=700V	−	−	1.0	mA
		Vcb=700V,Tc=100℃			5.0	
h_{FE}	DC Current Gain	Vce=5V,Ic=5.0A	10	−	40	
		Vce=5V,Ic=8.0A	6	−	40	
ts	**Resistive Load** Storage time	V_{CC}=125V,Ic=6.0A I_{B1}=1.6A,I_{B2}=−1.6A T_{P}=25μs	−	1.5	3.0	μs
tf	Fall Time			0.17	0.4	
ts	**Inductive Load** Storage Time	V_{CC}=15V,Ic=5A I_{B1}=1.6A,Vbe(off)=5V L=0.35mH,Vclamp=300V	−	0.8	2.0	μs
tf	Fall Time		−	0.04	0.1	
ts	**Inductive Load** Storage Time	V_{CC}=15V,Ic=1A I_{B1}=0.4A,Vbe(off)=5V L=0.2mH,Vclamp=300V Tc=100℃	−	0.8	2.5	μs
tf	Fall Time		−	0.05	0.15	

Note:

Pulse Test : Pulse Width300,Duty cycle 2%

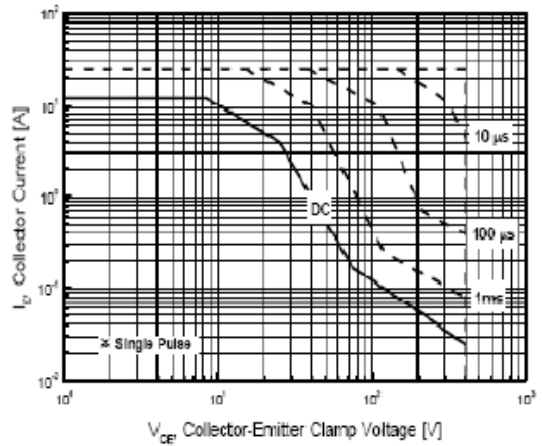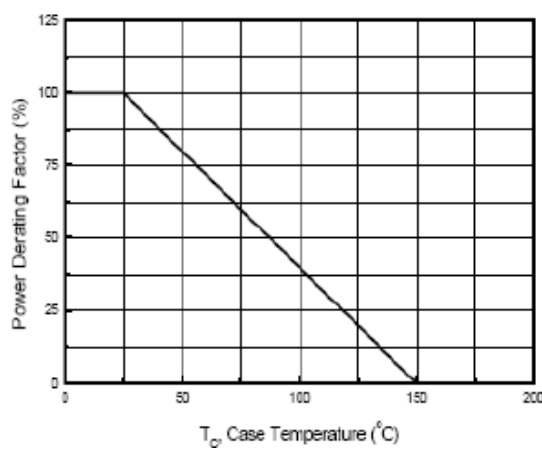*Steady, keep you advance*
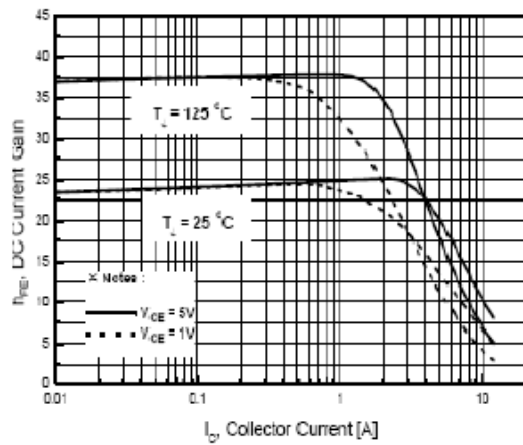
Fig.1 DC Current Gain
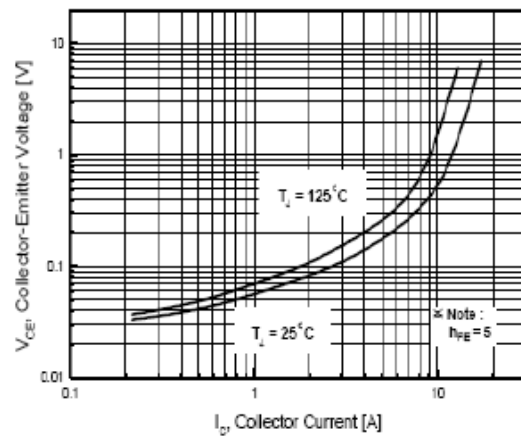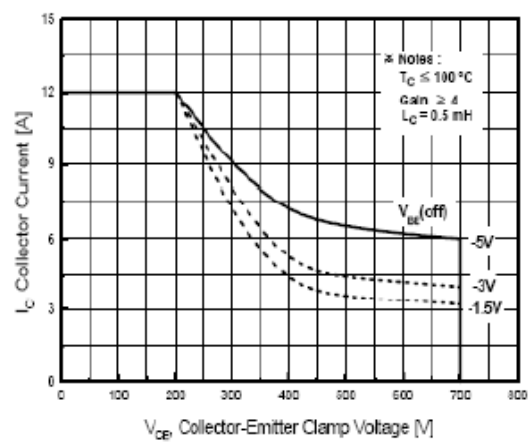

Fig.2 Collector -Emitter Saturation Voltage
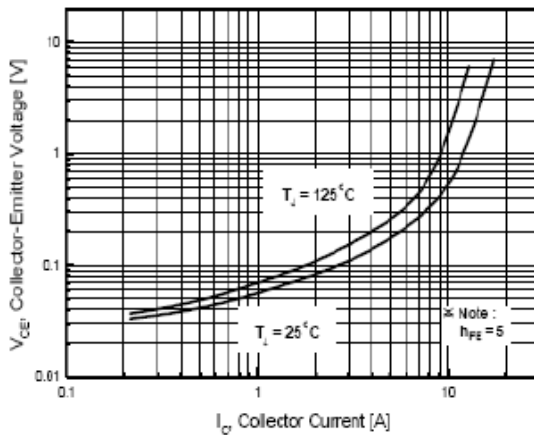
Fig.3 Bade-Emitter Saturation Voltage

Fig.4 Safe Operation Area
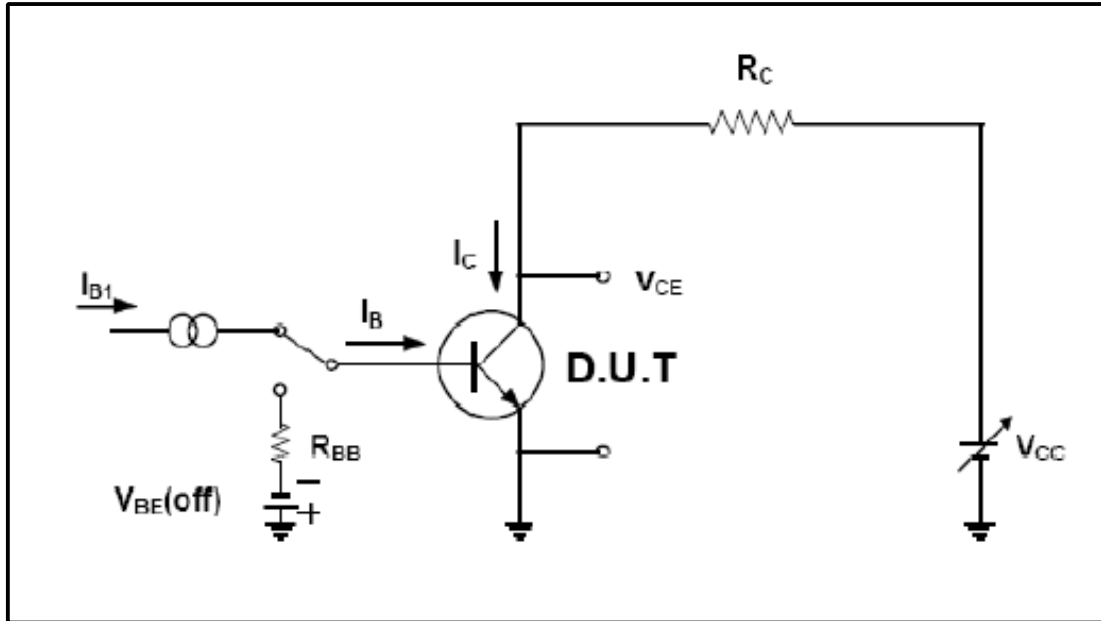

Fig.5 Power Derating
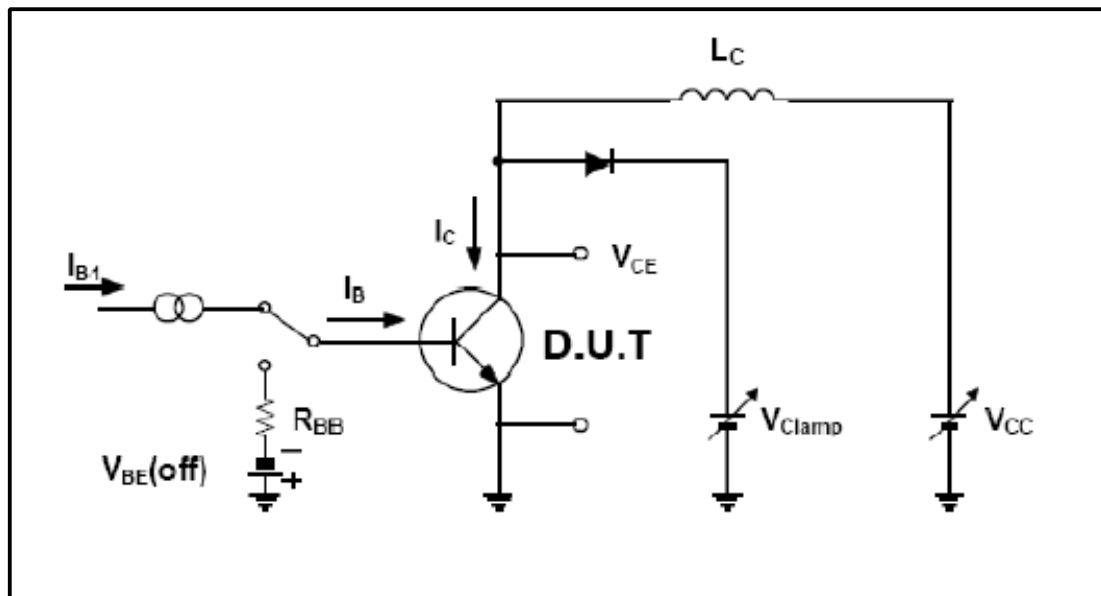

Fig.6 Reverse Biased Safe Operation Area

Steady, keep you advance

Resistive Load Switching Test Circuit

Inductive Load Switching & RBSOA Test Circuit

Steady, keep you advance

To-220 Package Dimension

Unit:mm

Steady, keep you advance